

ABSTRACT OF THE DISCLOSURE

Provided is a 3-5 group compound semiconductor comprising a GaAs substrate, a buffer layer on said GaAs substrate and an epitaxial crystal layer on said buffer layer, and the dislocation density in the epitaxial crystal layer on said buffer layer is $2000/\text{cm}^2$ or less. The properties and reliability of an electronic device or optical device can be remarkably improved.

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